Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	1	"5458518".pn.	US-PGPUB; USPAT	OR -	OFF	2005/01/21 14:49
L2	12	("5228878"   "5389026").PN. OR ("5458518").URPN.	US-PGPUB; USPAT; USOCR	OR	OFF	2005/01/21 14:52
L3	42	("3665241"   "3755704"	US-PGPUB;	OR	OFF	2005/01/21 14:59
		"3812559"   "3954523"   "4016017"   "4266233"   "4652467"     "4857161"   "4987101"   "5103288"	USPAT; USOCR			
		"5142184"   "5186670"   "5194780"   "5229331"   "5259799"				
	7.	"5529524"   "5569058"   "5578896"   "5585301"   "5597444"				
		"5653619"   "5663608"   "5684356"   "5712534"   "5793154"     "5804910"   "5853492"   "5869169"				
		"5898258"   "6028322"     "6232705"   "6251470"   "6255156"				
	Amily Marketine	"6277765"   "6333215").PN. OR ("6835111").URPN.				
L4	16	3 and (porous porosity pores)	US-PGPUB; USPAT	OR	OFF	2005/01/21 16:17
L15	. 12	("5228878"   "5389026").PN. OR ("5458518").URPN.	US-PGPUB; USPAT;	OR	OFF.	2005/01/21 19:03
L16	4). 4. 2. 4. <b>1</b>	"20040189175"	USOCR US-PGPUB; USPAT	OR	OFF	2005/01/21 20:02
L17	2	((polishing with (mechanic\$3 chemical\$3) with silicon) same planariz\$6) and 445/24.ccls.	US-PGPUB; USPAT	OR	OFF	2005/01/21 20:04
S1	86	(445/24,49-51.ccls. 438/20.ccls.) and (electron near3 (emitter emission emissive emitting)) and (tip micro\$tip micro\$point acicular cone) and silicon and (porosity porous pore)	US-PGPUB; USPAT	OR	ON	2005/01/21 14:48
<b>S2</b>	12	("3970887"   "4144636"   "4252833"   "4338164"   "4380865"   "4801380"   "5141459"   "5173634"   "519 <u>12</u> 17"   "5203 <u>7</u> 31"	ÜS-PGPUB; USPAT; USOCR	OR	ON	2004/12/14 18:50
		"5219310"   "5302238") PN.				

S3	64	(445/24,49-51.ccls. 438/20.ccls.)	US-PGPUB;	OR	ON	2004/12/14 18:51
33		and (electron near3 (emitter emission emissive emitting)) and (tip micro\$tip micro\$point acicular cone) and silicon and (porosity porous pore) and (poly\$crystal\$5 crystal\$5)	USPAT	OK	ON	2004/12/14 16.31
S4	0	(electron near3 (emitter emission emissive emitting)) and (tip micro\$tip micro\$point acicular cone) and silicon and (porosity porous pore) and (poly\$crystal\$5 crystal\$5)	EPO; JPO; DERWENT	OR	ON	2004/12/14 18:52
S5	77	(electron near3 (emitter emission emissive emitting)) and silicon and (porosity porous pore) and (poly\$crystal\$5 crystal\$5)	EPO; JPO; DERWENT	OR	ON	2004/12/14 18:52
<b>S6</b>	1096	("445"/\$.ccls. "438"/\$.ccls.) and (silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:15
S7	705	("445"/\$.ccls. "438"/\$.ccls.) and (silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity)) and oxidiz\$3	US-PGPUB; USPAT	OR	ON	2004/12/14 19:16
S8	274	("445"/\$.ccls. "438"/\$.ccls.) and (silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity)) and oxidiz\$3 and anodiz\$3	US-PGPUB; USPAT	OR	ON	2004/12/14 19:22
S9	20	("445"/\$.ccls. "438"/\$.ccls.) and (silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity)) and oxidiz\$3 and anodiz\$3 and ((field electron) near3 (emission emitter emissive emitting))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:26
S10	45	(silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity)) and oxidiz\$3 and anodiz\$3 and ((field electron) near3 (emission emitter emissive emitting))	US-PGPUB; USPAT	OR	ON	2004/12/14 19:27
S11	8	(silicon with (poly\$crystal\$5 crystal\$5)) and (silicon with (pore porous porosity)) and oxidiz\$3 and anodiz\$3 and ((field electron) near3 (emission emitter emissive emitting))	EPO; JPO; DERWENT	OR	ON	2004/12/14 19:26
S12	25	S10 not S9	US-PGPUB; USPAT	OR	ON	2004/12/15 17:23

S13	1	"6464853".pn.	US-PGPUB; USPAT	OR	ON	2004/12/15 17:18
S14	136	(silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (anodiz\$3 anodization) and (dielectric insulator insulat\$3 isolat\$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 18:45
S15	14	("5430300").URPN.	USPAT	OR	ON	2004/12/15 17:38
S16	40	("3665241"   "3755704"   "3812559"   "3954523"   "4016017"   "4266233"   "4652467"   "4857161"   "4987101"   "5103288"   "5142184"   "5186670"   "5194780"   "5229331"   "5259799"   "5358908"   "5430300"   "5458518"   "5470801"   "5473222"   "5483067"   "5529524"   "5569058"   "5578896"   "5585301"   "5597444"   "5653619"   "5663608"   "5684356"   "5712534"   "5793154"   "5804910"   "5869169"   "5898258"   "6028322"   "6232705"   "6257765"   "6333215").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/15 17:50
S17	2	("5228878"   "5389026").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2004/12/15 18:05
S18	9	("5458518").URPN.	USPAT	OR	ON:	2004/12/15 18:06
S19	9	("3755704"   "4652467"   "4940916"   "4987101"   "5103288"   "5194780"   "5225820"   "5393712"   "5430300").PN.	US-PGPUB; USPAT; USOCR	OR	ON .	2004/12/15 18:34
S20	4	(silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (anodiz\$3 anodization) and (dielectric insulator insulat\$3 isolat\$3) and (((field electron) near3 (emission emissive emitting emitter)) FED) (silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (anodiz\$3 anodization) and (dielectric insulator insulat\$3 isolat\$3) and (((field electron))	USOCR; EPO; JPO EPO; JPO; DERWENT	OR OR	ON ON	2004/12/15 18:46

S22	15	(silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (anodiz\$3 anodization) and (((field electron) near3 (emission emissive emitting emitter)) FED)	EPO; JPO; DERWENT	OR	ON	2004/12/15 18:53
S23	93	(silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	EPO; JPO; DERWENT	OR	ON	2004/12/15 19:10
S24	1231	(silicon with (pore porosity porous)) and (oxidat\$3 oxidiz\$3) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 19:10
S25	272	((silicon with (pore porosity porous)) same (oxidat\$3 oxidiz\$3)) and (((field electron) near3 (emission emissive emitting emitter)) FED)	US-PGPUB; USPAT	OR	ON	2004/12/15 19:10